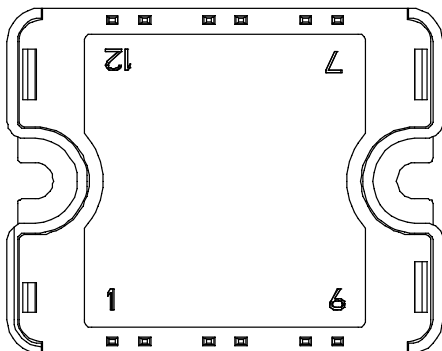
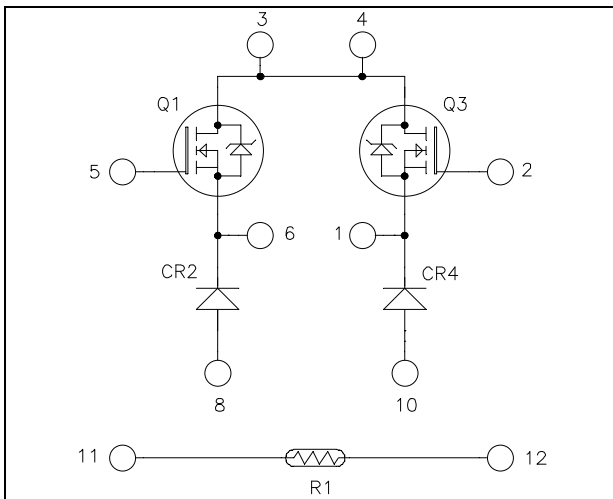


## Dual Buck chopper Super Junction MOSFET Power Module

$V_{DSS} = 900V$   
 $R_{DSon} = 120m\Omega \text{ max @ } T_j = 25^\circ C$   
 $I_D = 30A \text{ @ } T_c = 25^\circ C$



Pins 3/4 must be shorted together

### Application

- AC and DC motor control
- Switched Mode Power Supplies

### Features

- **COOLMOS** Power Semiconductors
  - Ultra low  $R_{DSon}$
  - Low Miller capacitance
  - Ultra low gate charge
  - Avalanche energy rated
  - Very rugged
- Very low stray inductance
  - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a single buck of twice the current capability
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	900	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	30
		$T_c = 80^\circ C$	23
$I_{DM}$	Pulsed Drain current	75	A
$V_{GS}$	Gate - Source Voltage	$\pm 20$	V
$R_{DSon}$	Drain - Source ON Resistance	120	$m\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	250
$I_{AR}$	Avalanche current (repetitive and non repetitive)		8.8
$E_{AR}$	Repetitive Avalanche Energy		2.9
$E_{AS}$	Single Pulse Avalanche Energy		1940

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

**All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified**

**Electrical Characteristics**

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 900V	T <sub>j</sub> = 25°C		100	μA	
		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 900V	T <sub>j</sub> = 125°C	500			
R <sub>DS(on)</sub>	Drain – Source on Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 26A		100	120	mΩ	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 3mA		2.5	3	3.5	V
I <sub>GSS</sub>	Gate – Source Leakage Current	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0V			100	nA	

**Dynamic Characteristics**

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0V ; V <sub>DS</sub> = 100V		6.8		nF
C <sub>oss</sub>	Output Capacitance	f = 1MHz		0.33		
Q <sub>g</sub>	Total gate Charge	V <sub>GS</sub> = 10V V <sub>Bus</sub> = 400V I <sub>D</sub> = 26A		270		nC
Q <sub>gs</sub>	Gate – Source Charge			32		
Q <sub>gd</sub>	Gate – Drain Charge			115		
T <sub>d(on)</sub>	Turn-on Delay Time	<b>Inductive Switching (125°C)</b> V <sub>GS</sub> = 10V V <sub>Bus</sub> = 600V I <sub>D</sub> = 26A R <sub>G</sub> = 7.5Ω		70		ns
T <sub>r</sub>	Rise Time			20		
T <sub>d(off)</sub>	Turn-off Delay Time			400		
T <sub>f</sub>	Fall Time			25		
E <sub>on</sub>	Turn-on Switching Energy	<b>Inductive switching @ 25°C</b> V <sub>GS</sub> = 10V ; V <sub>Bus</sub> = 600V I <sub>D</sub> = 26A ; R <sub>G</sub> = 7.5Ω		1.5		mJ
E <sub>off</sub>	Turn-off Switching Energy			0.75		
E <sub>on</sub>	Turn-on Switching Energy	<b>Inductive switching @ 125°C</b> V <sub>GS</sub> = 10V ; V <sub>Bus</sub> = 600V I <sub>D</sub> = 26A ; R <sub>G</sub> = 7.5Ω		2.1		mJ
E <sub>off</sub>	Turn-off Switching Energy			0.85		

**Chopper diode ratings and characteristics**

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage		1200			V
I <sub>RM</sub>	Maximum Reverse Leakage Current	V <sub>R</sub> = 1200V	T <sub>j</sub> = 25°C		100	μA
			T <sub>j</sub> = 125°C		500	
I <sub>F</sub>	DC Forward Current			30		A
V <sub>F</sub>	Diode Forward Voltage	I <sub>F</sub> = 30A		2.6	3.1	V
		I <sub>F</sub> = 60A		3.2		
		I <sub>F</sub> = 30A	T <sub>j</sub> = 125°C	1.8		
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 30A V <sub>R</sub> = 800V di/dt = 200A/μs	T <sub>j</sub> = 25°C	300		ns
			T <sub>j</sub> = 125°C	380		
Q <sub>rr</sub>	Reverse Recovery Charge	I <sub>F</sub> = 30A V <sub>R</sub> = 800V di/dt = 200A/μs	T <sub>j</sub> = 25°C	360		nC
			T <sub>j</sub> = 125°C	1700		

**Thermal and package characteristics**

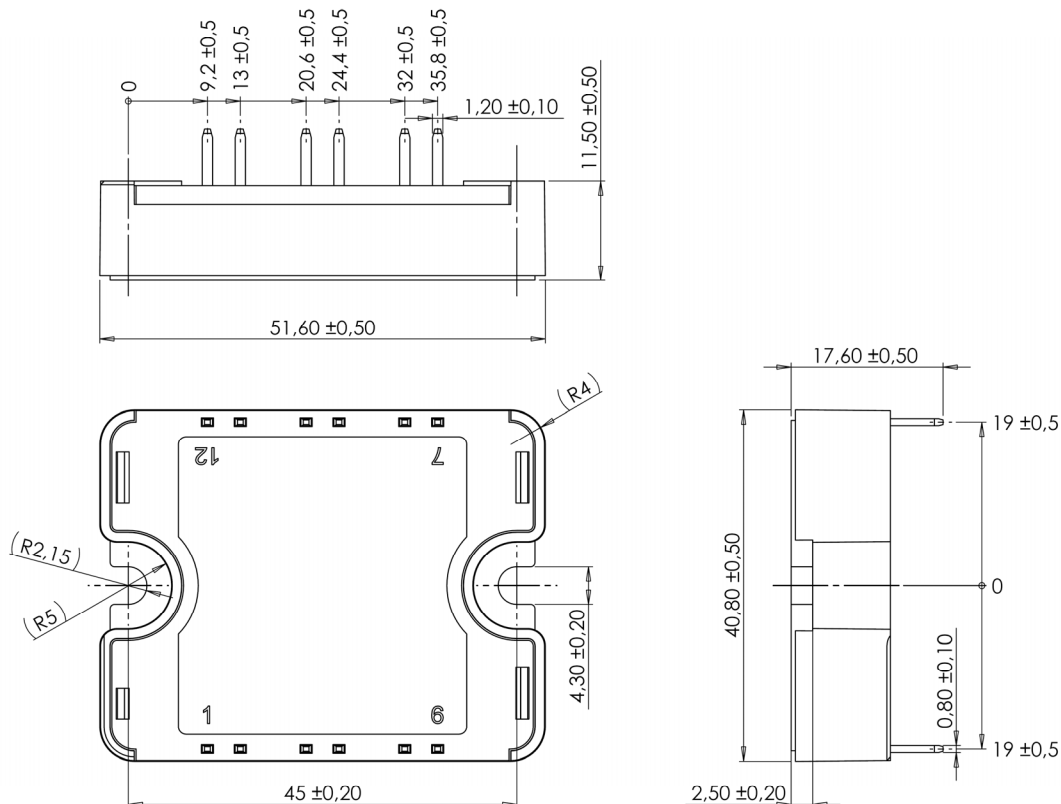
Symbol	Characteristic	Min	Typ	Max	Unit	
R <sub>thJC</sub>	Junction to Case Thermal Resistance	CoolMOS		0.50	°C/W	
		diode		1.2		
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz	4000			V	
T <sub>J</sub>	Operating junction temperature range	-40		150	°C	
T <sub>STG</sub>	Storage Temperature Range	-40		125		
T <sub>C</sub>	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				80	g

**Temperature sensor NTC** (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
ΔR <sub>25</sub> /R <sub>25</sub>			5		%
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		3952		K
ΔB/B		T <sub>C</sub> =100°C	4		%

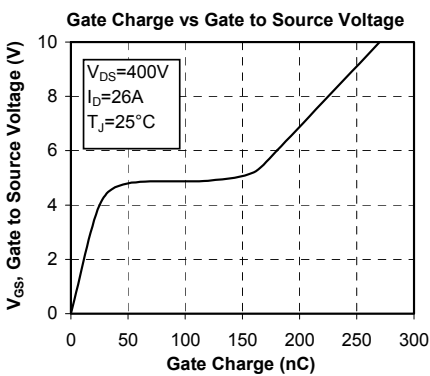
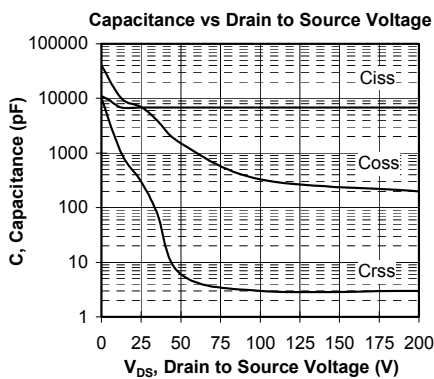
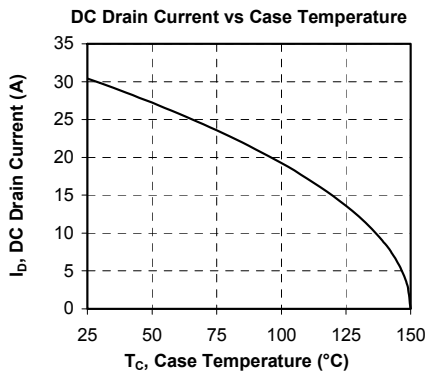
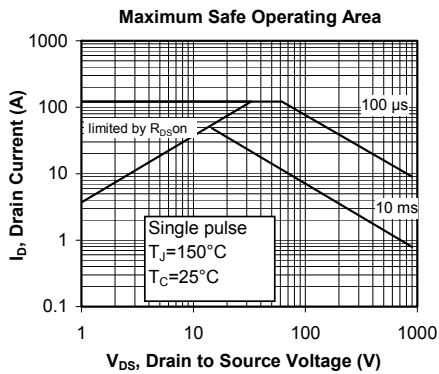
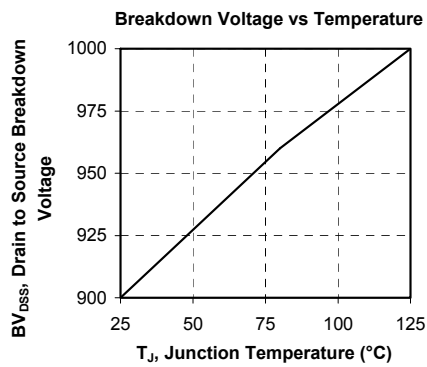
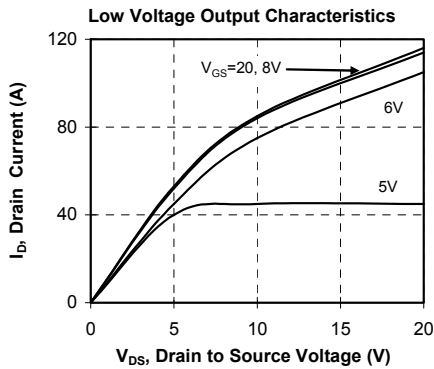
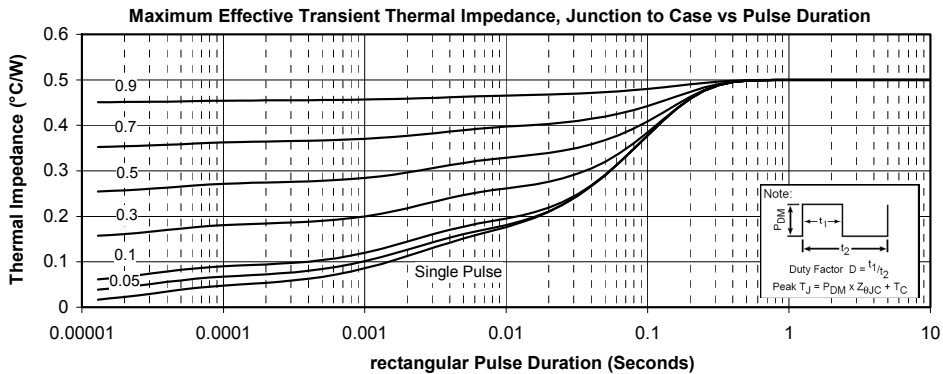
$$R_T = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

T: Thermistor temperature  
 R<sub>T</sub>: Thermistor value at T

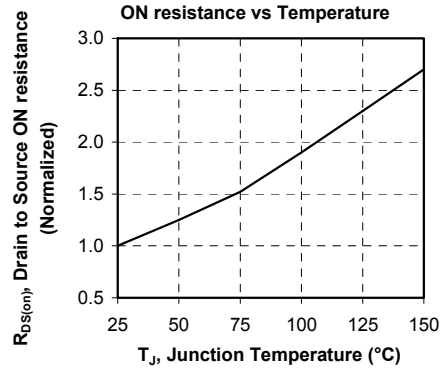
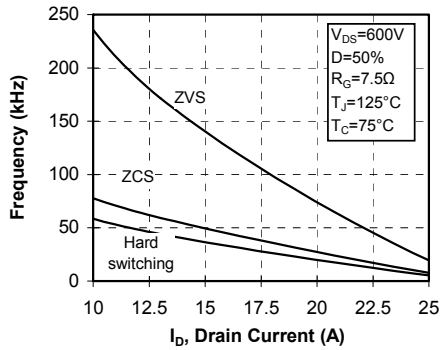
**SP1 Package outline** (dimensions in mm)


See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

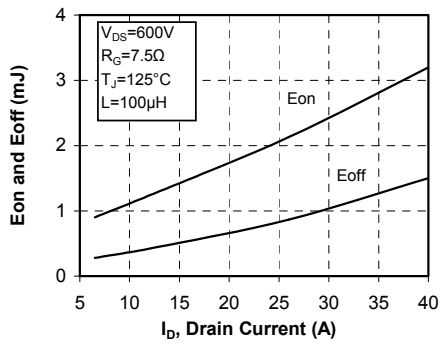
## Typical CoolMOS performance Curve



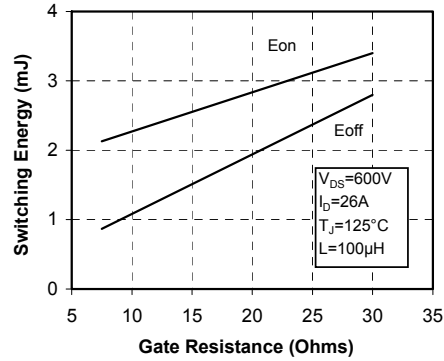
**Operating Frequency vs Drain Current**



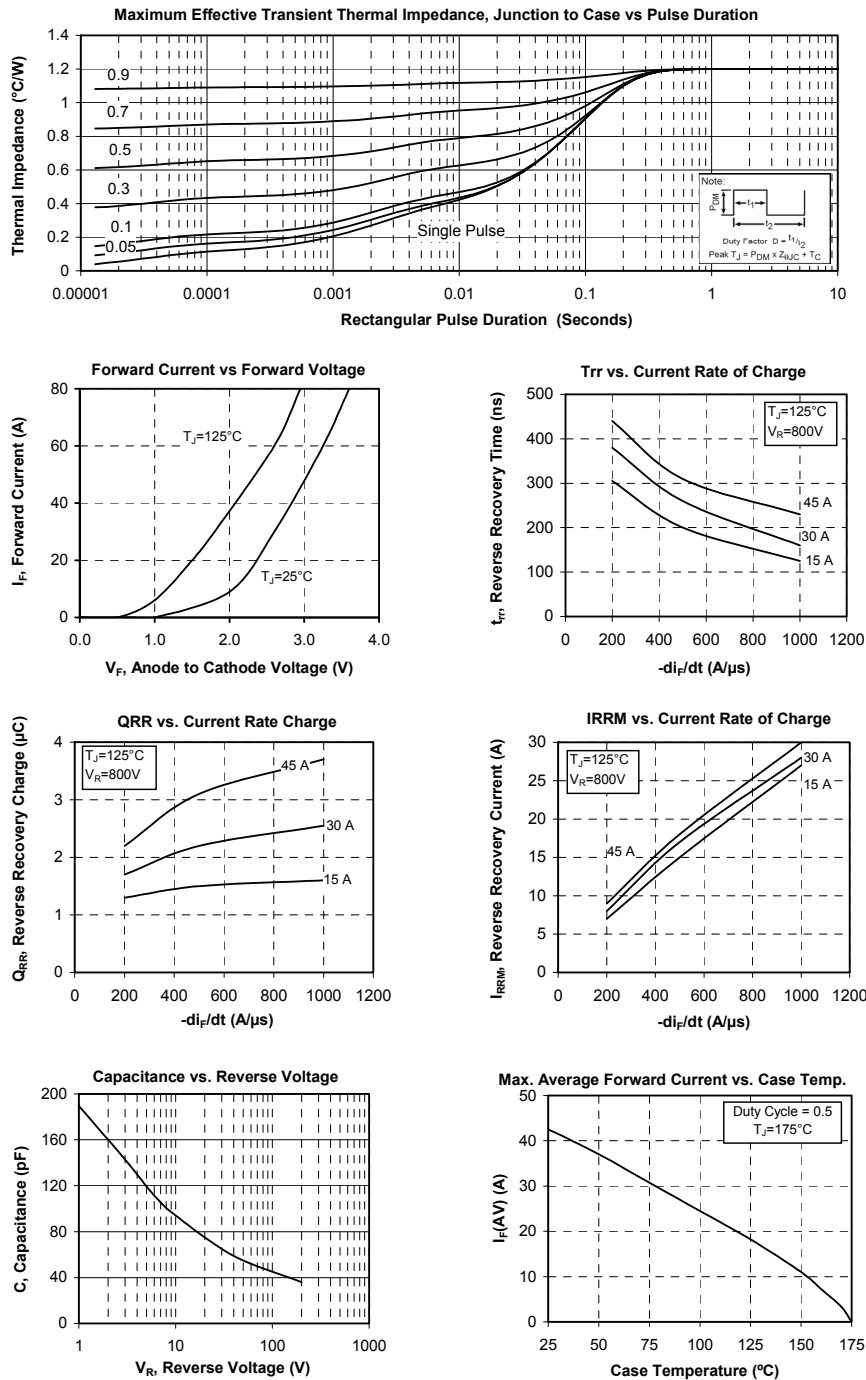
**Switching Energy vs Current**



**Switching Energy vs Gate Resistance**



## Typical Chopper diode performance Curve



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